



# PBSS2515MB

15 V, 0.5 A NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 1 — 26 January 2012

Product data sheet

## 1. Product profile

### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS3515MB.

### 1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High efficiency due to less heat generation
- AEC-Q101 qualified
- Reduced Printed-Circuit Board (PCB) requirements

### 1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

### 1.4 Quick reference data

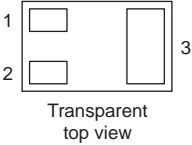
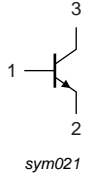
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	15	V
$I_C$	collector current		-	-	500	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	1	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 500$ mA; $I_B = 50$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	360	500	m $\Omega$



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	E	emitter		
3	C	collector		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS2515MB	-	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

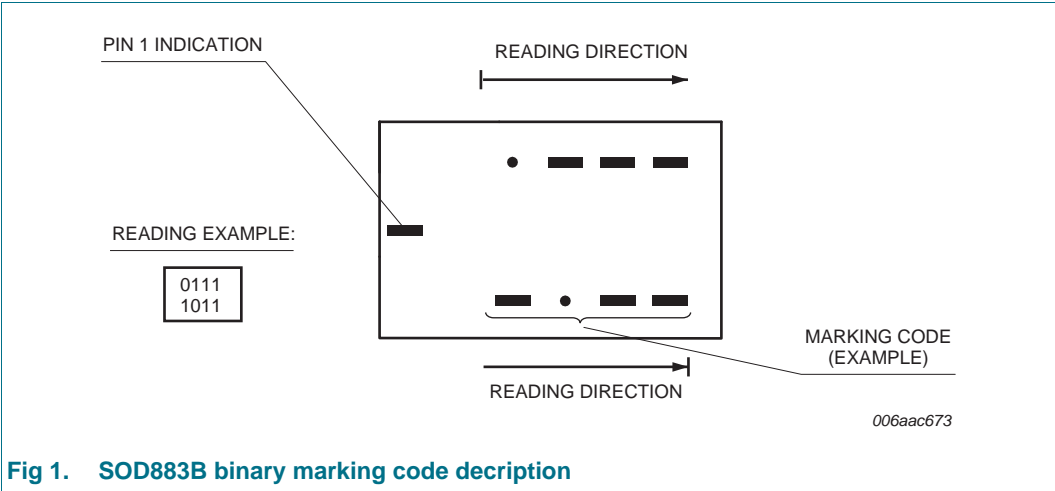
4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBSS2515MB	0001 0001

[1] For SOT883B binary marking code description, see [Figure 1](#).

4.1 Binary marking code description



## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	15	V
$V_{CEO}$	collector-emitter voltage	open base	-	15	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
$I_C$	collector current		-	500	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	1	A
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	<a href="#">[1]</a> <a href="#">[2]</a>	250	mW
			<a href="#">[3]</a> <a href="#">[2]</a>	590	mW
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-55	150	°C
$T_{stg}$	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	500	K/W
			[3][2]	-	-	212	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

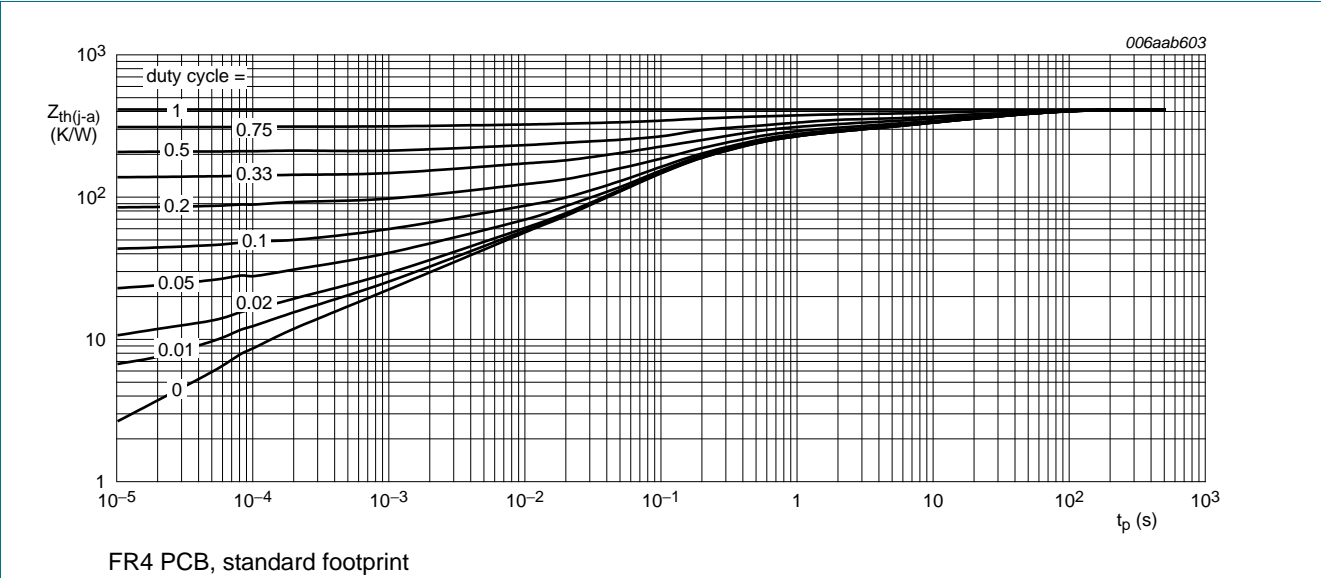


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

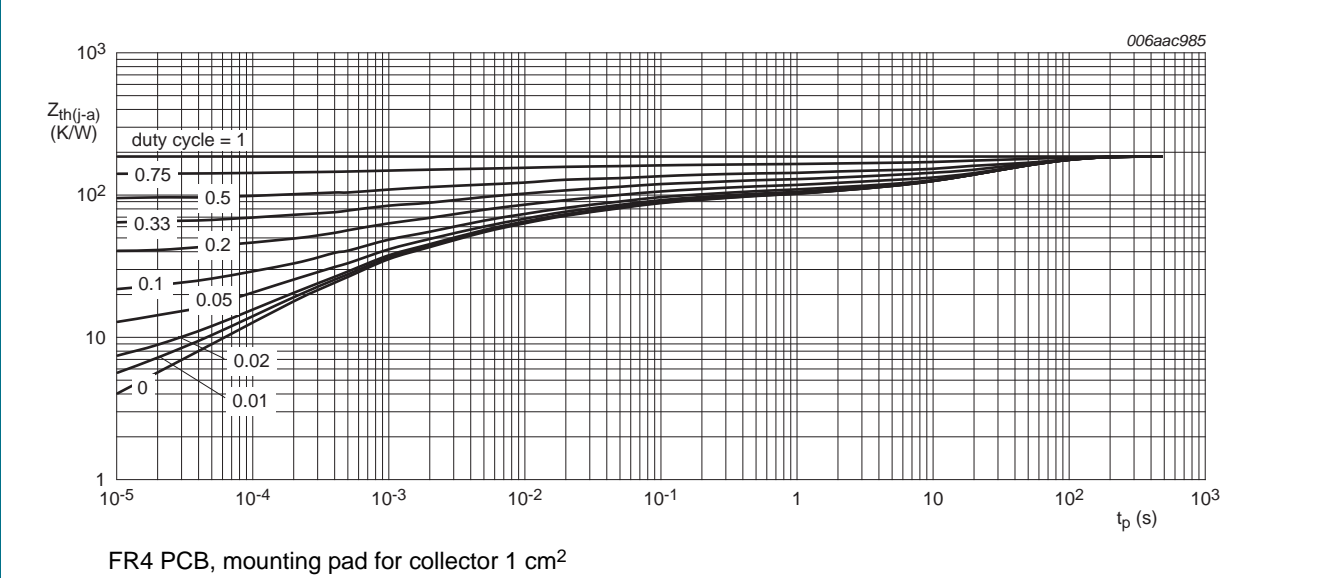
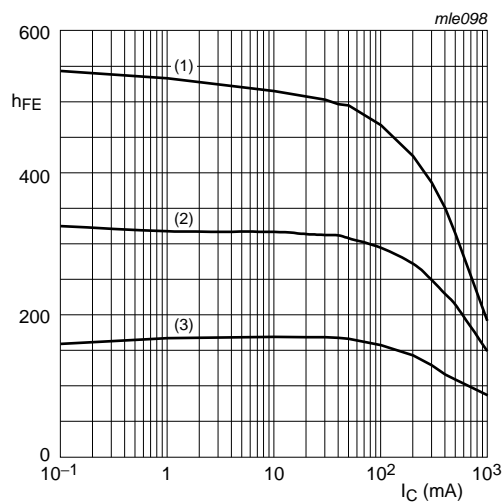


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

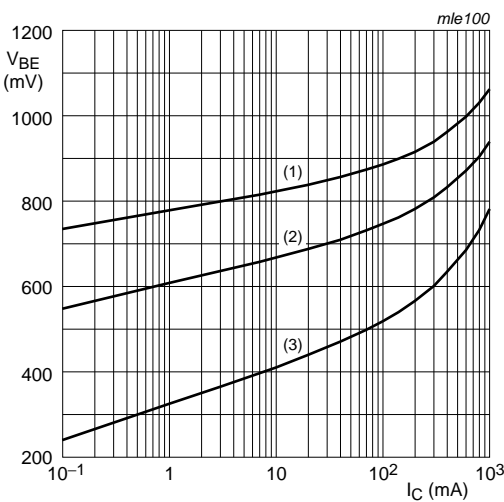
**Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 15\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{CB} = 15\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}; T_{amb} = 25\text{ }^{\circ}\text{C}$	200	-	-	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	150	-	-	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	90	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	25	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	150	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	250	mV
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	360	500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	0.9	V
$f_T$	transition frequency	$V_{CE} = 5\text{ V}; I_C = 100\text{ mA}; f = 100\text{ MHz};$ $T_{amb} = 25\text{ }^{\circ}\text{C}$	250	420	-	MHz
$C_C$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	4.4	6	pF



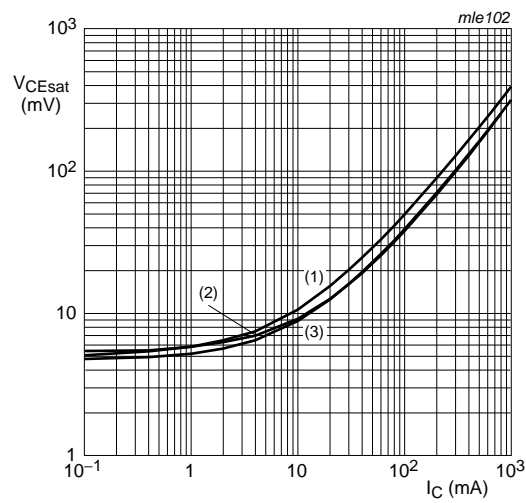
$V_{CE} = 2\text{ V}$   
(1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
(2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
(3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 4. DC current gain as a function of collector current; typical values



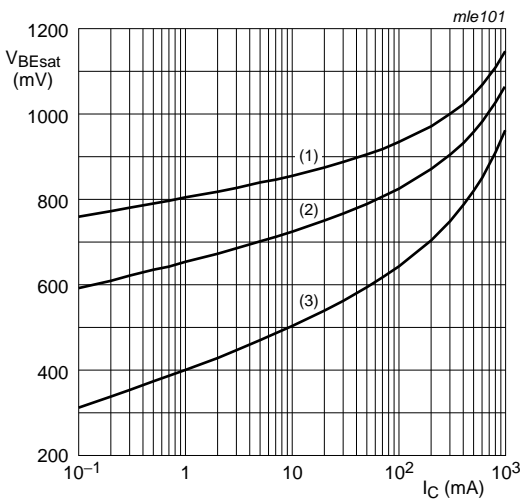
$V_{CE} = 2\text{ V}$   
(1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
(2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
(3)  $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 5. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$   
(1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
(2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
(3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$   
(1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
(2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
(3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values

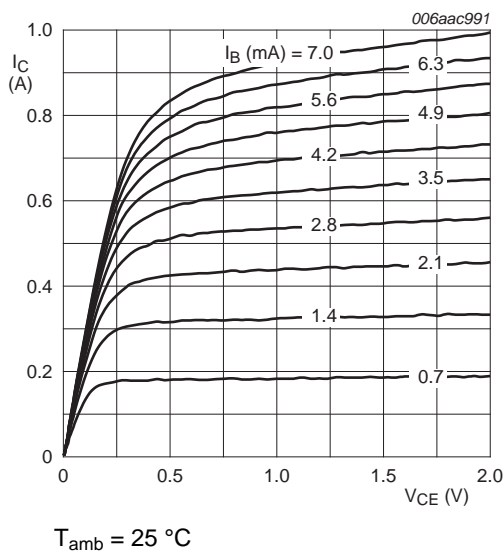
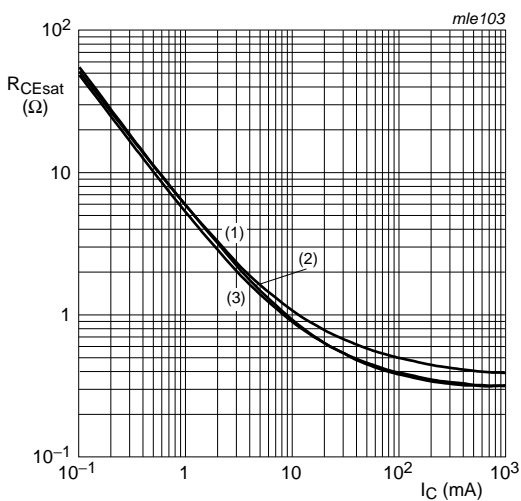


Fig 8. Collector current as a function of collector-emitter voltage; typical values



$I_C/I_B = 20$   
(1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
(2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
(3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 9. Collector-emitter equivalent on-resistance as a function of collector current; typical values

## 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors and is suitable for use in automotive applications.

9. Package outline



Fig 10. Package outline SOT883B

10. Soldering

Footprint information for reflow soldering

SOT883B

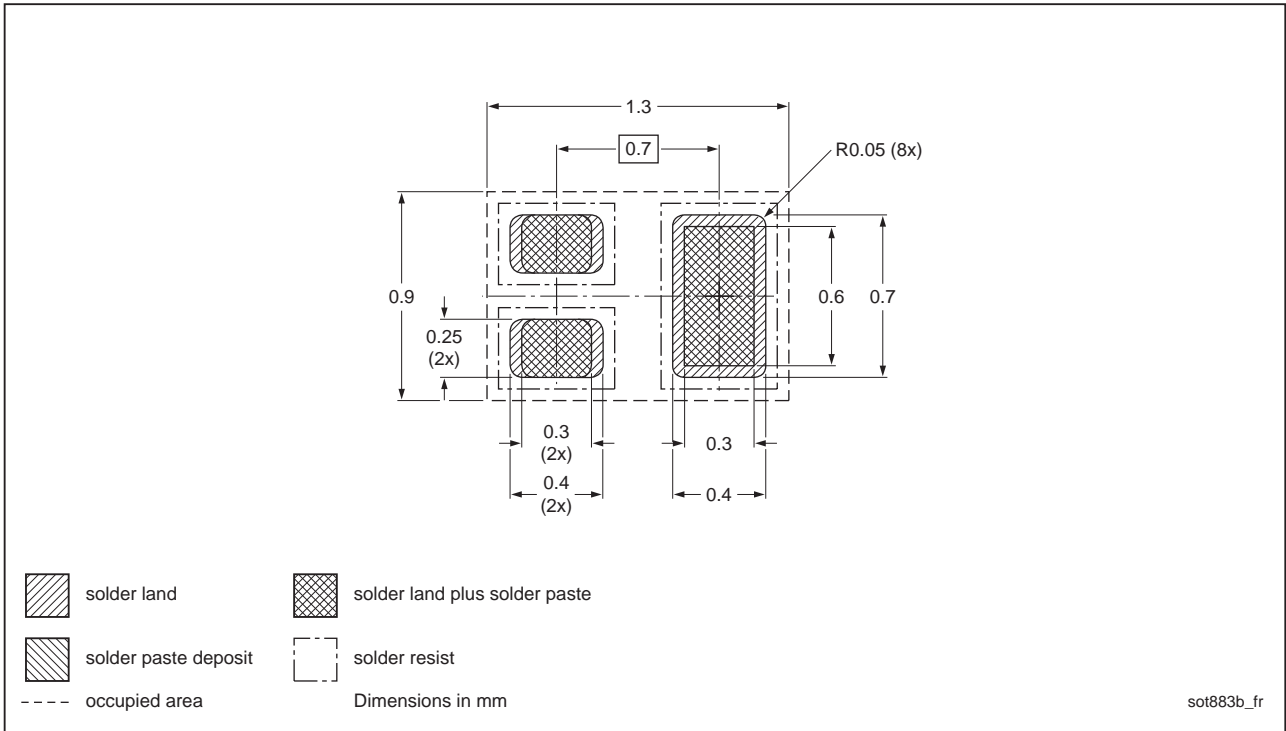


Fig 11. Reflow soldering footprint for SOT883B



## 11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS2515MB v.1	20120126	Product data sheet	-	-

## 12. Legal information

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Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Date of release: 26 January 2012

Document identifier: PBSS2515MB